

# AOS Semiconductor Product Reliability Report

**AON7410**, rev C

**Plastic Encapsulated Device** 

ALPHA & OMEGA Semiconductor, Inc <a href="https://www.aosmd.com">www.aosmd.com</a>



This AOS product reliability report summarizes the qualification result for AON7410. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AON7410 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

#### **Table of Contents:**

I. Product Description

II. Package and Die information

III. Reliability Stress Test Summary and Results

IV. Reliability Evaluation

### I. Product Description:

The AON7410 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This device is suitable for use in DC-DC converters and Load Switch applications.

Details refer to the datasheet.

# II. Die / Package Information:

**AON7410** 

Process Standard sub-micron

30V N-Channel MOSFET

Package TypeDFN3x3 EPLead FrameBare CuDie AttachAg EpoxyBondCu wire

Mold Material Epoxy resin with silica filler

Moisture Level Up to Level 1



## III. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	GB Temp = 150°C , Vgs=100% of Vgsmax		924 pcs	0	JESD22-A108
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 / 1000 hours	924 pcs	0	JESD22-A108
MSL Precondition	168hr 85°C / 85%RH + 3 cycle reflow@260°C (MSL 1)	-	5082 pcs	0	JESD22-A113
HAST	HAST  130°C , 85%RH, 33.3 psi, Vds = 80% of Vdsmax  H3TRB  85°C , 85%RH, Vds = 80% of Vdsmax  121°C , 29.7psi, RH=100%		924 pcs	0	JESD22-A110
H3TRB			924 pcs	0	JESD22-A101
Autoclave			924 pcs	0	JESD22-A102
Temperature Cycle	•		924 pcs	0	JESD22-A104
HTSL	HTSL Temp = 150°C  Power Cycling Δ Tj = 100°C		693 pcs	0	JESD22-A103
			693 pcs	0	AEC Q101

Note: The reliability data presents total of available generic data up to the published date.

#### IV. Reliability Evaluation

FIT rate (per billion): 3.43 MTTF = 33270 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate =  $\text{Chi}^2 \times 10^9 \text{/} [2 \text{ (N) (H) (Af)}] = 3.43$ MTTF =  $10^9 / \text{FIT} = 33270 \text{ years}$ 

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from burn-in tests

**H** = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [Af] = Exp [Ea / k (1/Tj u - 1/Tj s)]

**Acceleration Factor ratio list:** 

		55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C		
Α	f	259	87	32	13	5.64	2.59	1		

**Tj s** = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** =The use junction temperature in degree (Kelvin), K = C+273.16

 $\mathbf{k}$  = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K